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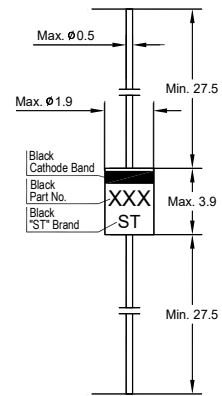
Silicon Epitaxial Planar Switching Diode

Features

- Fast switching speed
- High reliability

Applications

- For general purpose switching applications



Glass Case DO-35
Dimensions in mm

Absolute Maximum Ratings ($T_a = 25\text{ }^\circ\text{C}$)

Parameter	Symbol	Value	Unit
Non-Repetitive Peak Reverse Voltage	V_{RM}	50	V
Forward Continuous Current	I_{FM}	300	mA
Average Rectified Forward Current	$I_{F(AV)}$	200	mA
Power Dissipation	P_{tot}	500	mW
Junction Temperature	T_j	200	$^\circ\text{C}$
Operating and Storage Temperature Range	T_{stg}	- 65 to + 175	$^\circ\text{C}$

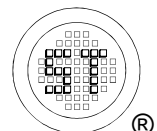
Characteristics at $T_a = 25\text{ }^\circ\text{C}$

Parameter	Symbol	Max.	Unit
Thermal Resistance Junction to Ambient ¹⁾	$R_{\theta JA}$	350	$^\circ\text{C/W}$

¹⁾ Valid provided that leads are at a distance of 8 mm from case kept at ambient temperature.

Characteristics at $T_a = 25\text{ }^\circ\text{C}$

Parameter	Symbol	Max.	Unit
Forward Voltage at $I_F = 200\text{ mA}$	V_F	1.2	V
Reverse Current at $V_R = 50\text{ V}$	I_R	100	nA
Reverse Recovery Time at $I_F = I_R = 200\text{ mA}$, $I_{rr} = 0.1 \times I_R$, $R_L = 100\ \Omega$	t_{rr}	4	ns



Electrical Characteristics Curves

Fig 1. Forward Characteristics

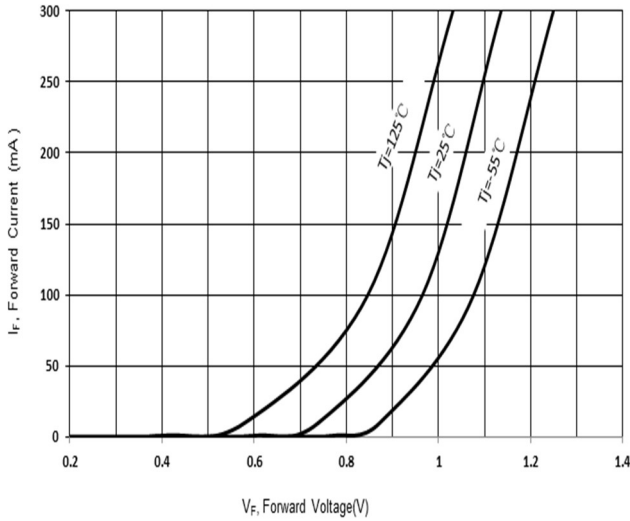


Fig 2. Reverse Characteristics

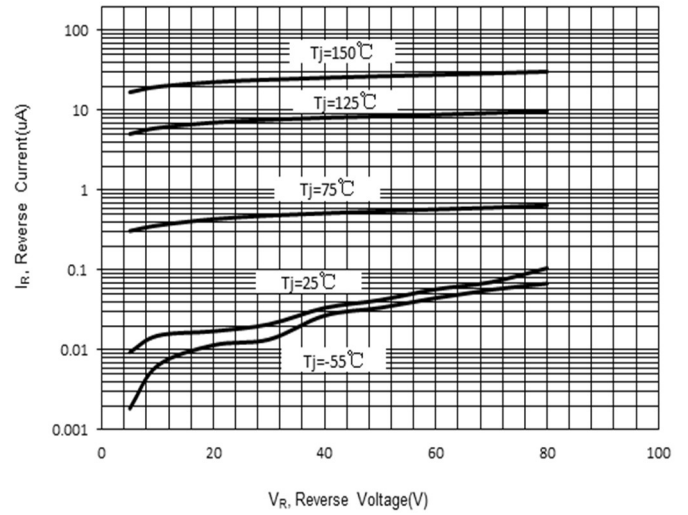


Fig 3. Junction Capacitance

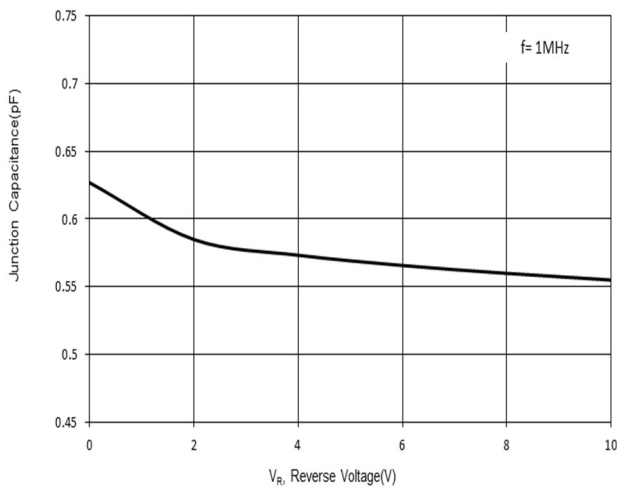


Fig 4. Power Derating Curves

